1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: I_{F(AV)} ≤ 3 A
- Reverse voltage: V_R ≤ 60 V
- Low forward voltage
- High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified
- High temperature T_i ≤ 175 °C

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 165 °C; square wave	-	-	3	Α
V_R	reverse voltage	T _j = 25 °C	-	-	60	V
V _F	forward voltage	I_F = 3 A; t_p ≤ 300 μs; δ ≤ 0.02 ; T_j = 25 °C; pulsed	-	420	475	mV
I _R	reverse current	T_j = 25 °C; V_R = 60 V; pulsed	-	115	400	μΑ





High-temperature 60 V, 3 A Schottky barrier rectifier

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]	4	1 [[-] 2
2	A	anode	SOD128	sym001

^[1] The marking bar indicates the cathode.

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG6030EVP	SOD128	plastic surface-mounted package; 2 leads	SOD128			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG6030EVP	DB

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _R	reverse voltage	T _j = 25 °C		-	60	V
I _F	forward current	T _{sp} = 160 °C		-	4.2	Α
I _{F(AV)}	average forward current	$\bar{\delta}$ = 0.5 ; f = 20 kHz; $T_{amb} \leq$ 95 °C; square wave	[1]	-	3	А
		δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 165 °C; square wave		-	3	А
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	70	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	750	mW
			[3]	-	1250	mW
			[1]	-	2500	mW
T _j	junction temperature			-	175	°C

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Symbol	Parameter	Conditions	Min	Max	Unit
T _{amb}	ambient temperature		-55	175	°C
T _{stg}	storage temperature		-65	175	°C

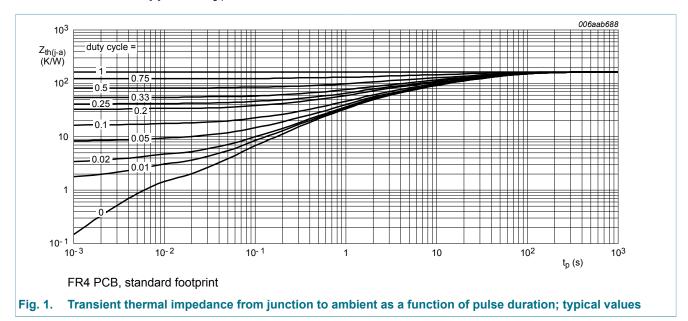
- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

9. Thermal characteristics

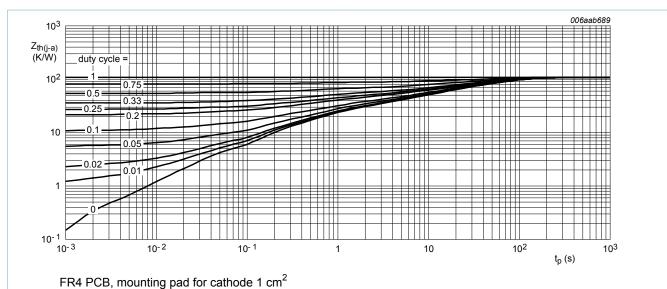
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistan from junction to ambient	thermal resistance	in free air	[1][2]	-	-	200	K/W
			[1][3]	-	-	120	K/W
	ambient		[1][4]	-	-	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	12	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.



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Treation, mounting pad for calmode 1 cm

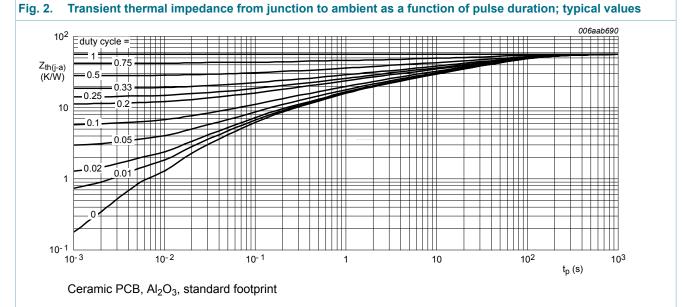


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

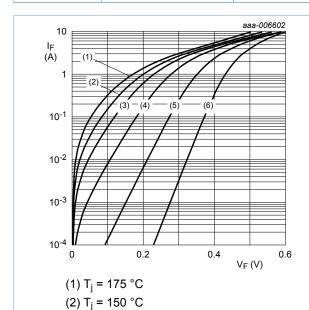
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage	I_F = 0.1 A; t_p ≤ 300 μs; δ ≤ 0.02 ; T_j = 25 °C; pulsed	-	275	310	mV
		$I_F = 0.5 \text{ A}; t_p \le 300 \text{ µs}; \delta \le 0.02;$ $T_j = 25 ^{\circ}\text{C}; \text{ pulsed}$	-	325	-	mV
		I_F = 1 A; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C; pulsed	-	355	400	mV

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I_F = 1.5 A; t_p ≤ 300 μs; \overline{o} ≤ 0.02 ; T_j = 25 °C; pulsed	-	375	-	mV
		I_F = 2 A; t_p ≤ 300 μs; δ ≤ 0.02 ; T_j = 25 °C; pulsed	-	390	440	mV
		I_F = 3 A; t_p ≤ 300 μs; δ ≤ 0.02 ; T_j = 25 °C; pulsed	-	420	475	mV
I _R	reverse current	V _R = 5 V; T _j = 25 °C; pulsed	-	7	20	μΑ
		V _R = 10 V; T _j = 25 °C; pulsed	-	9	40	μΑ
		V_R = 30 V; T_j = 25 °C; pulsed	-	20	80	μA
		V_R = 60 V; T_j = 25 °C; pulsed	-	115	400	μA
		V _R = 10 V; T _j = 125 °C; pulsed	-	9	-	mA
		V _R = 60 V; T _j = 125 °C; pulsed	-	70	300	mA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	575	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	200	-	pF
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}$; $I_R = 0.5 \text{ A}$; $I_{R(meas)} = 0.1 \text{ A}$; $I_{j} = 25 \text{ °C}$	-	20	-	ns
V_{FRM}	peak forward recovery voltage	$I_F = 1 \text{ A}; \text{ d}I_F/\text{d}t = 40 \text{ A/µs}; T_j = 25 ^{\circ}\text{C}$	-	385	-	mV

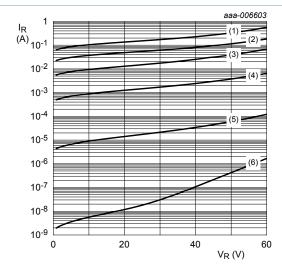


(3) $T_i = 125 \, ^{\circ}C$ (4) $T_i = 85 \, ^{\circ}C$

(5) $T_i = 25$ °C

(6) $T_i = -40 \, ^{\circ}C$

Forward current as a function of forward Fig. 4. voltage; typical values



(1) $T_i = 175 \,^{\circ}C$

(2) $T_j = 150 \, ^{\circ}\text{C}$

(3) $T_i = 125 \, ^{\circ}C$

(4) $T_i = 85 \, ^{\circ}C$

(5) $T_i = 25$ °C

(6) $T_j = -40 \, ^{\circ}C$

Reverse current as a function of reverse Fig. 5. voltage; typical values

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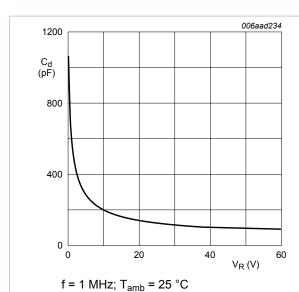
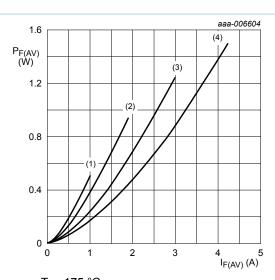


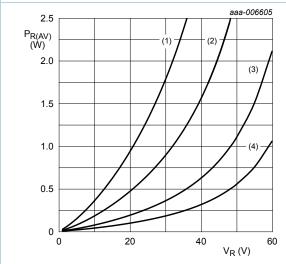
Fig. 6. Diode capacitance as a function of reverse voltage; typical values



 $T_j = 175 \,^{\circ}\text{C}$ (1) $\delta = 0.1$ (2) $\delta = 0.2$ (3) $\delta = 0.5$

 $(4) \delta = 1$



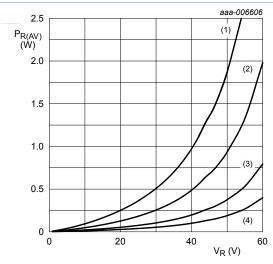


 $T_j = 150 \,^{\circ}\text{C}$ (1) $\delta = 1$

(2) $\delta = 0.5$ (3) $\delta = 0.2$

 $(4) \delta = 0.1$

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



 $T_j = 125 \,^{\circ}\text{C}$ (1) $\delta = 1$

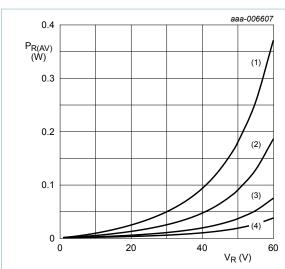
(2) $\delta = 0.5$

(3) $\delta = 0.2$

 $(4) \delta = 0.1$

Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values

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 $T_i = 85 \, ^{\circ}C$

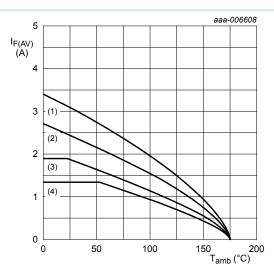
 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

 $(4) \delta = 0.1$

Fig. 10. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_i = 175 °C

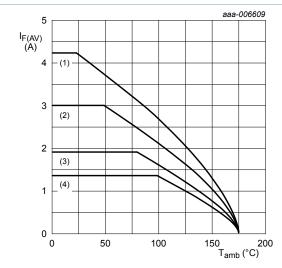
(1) δ = 1 (DC)

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

T_i = 175 °C

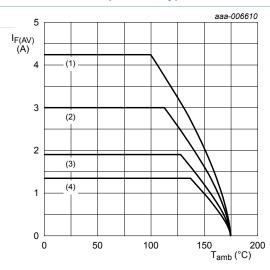
(1) $\delta = 1$ (DC)

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 12. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

 $T_i = 175 \,{}^{\circ}\text{C}$

 $(1) \delta = 1 (DC)$

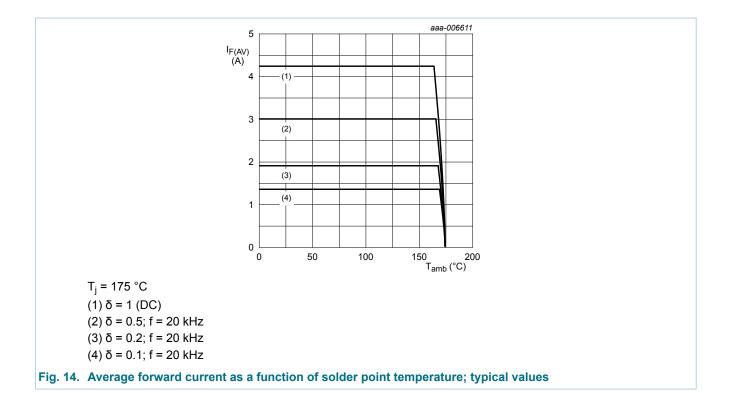
(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

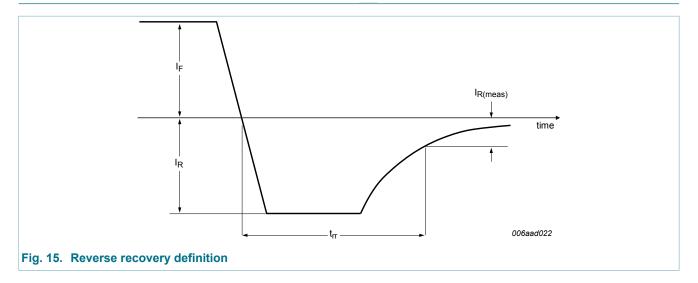
(4) δ = 0.1; f = 20 kHz

Fig. 13. Average forward current as a function of ambient temperature; typical values

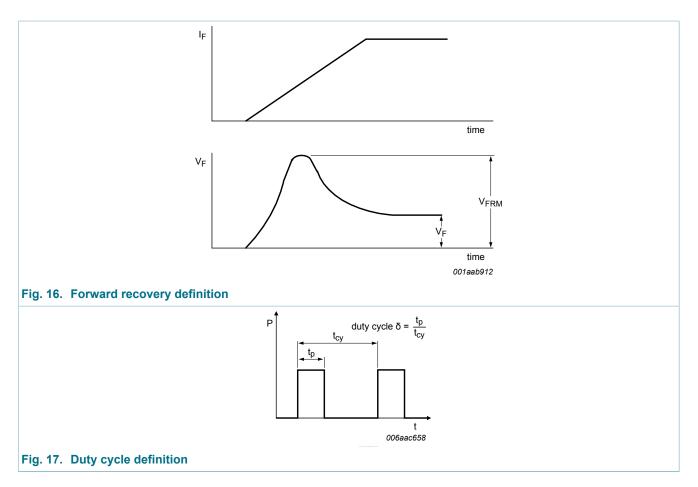
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11. Test information



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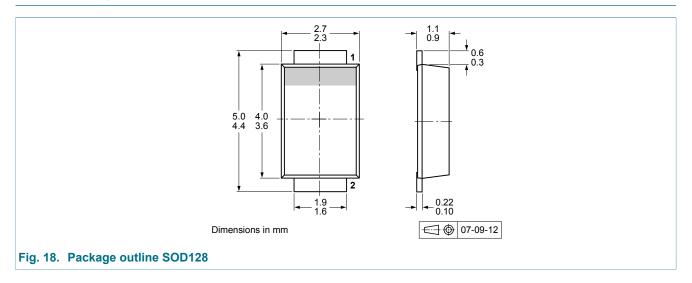
The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

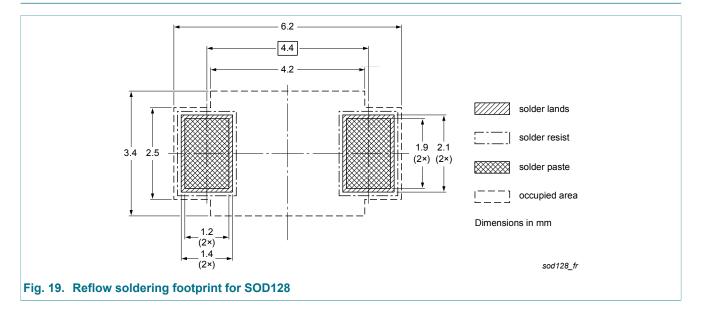
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6030EVP v.1	20130304	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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